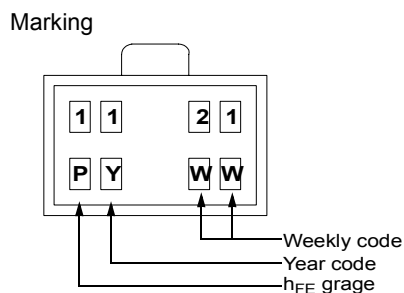
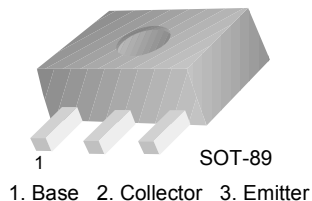


KSB1121

PNP Epitaxial Planar Silicon Transistor

High Current Driver Applications

- Low Collector-Emitter Saturation Voltage
- Large Current Capacity
- Fast Switching Speed
- Complement to KSD1621



Absolute Maximum Ratings $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{CBO}	Collector-Base Voltage	-30	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current	-2	A
P_C P_C^*	Collector Power Dissipation	500 1.3	mW W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	-55 ~ 150	$^\circ\text{C}$

* Mounted on Ceramic Board (250mm² x 0.8mm)

Electrical Characteristics $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = -10\mu\text{A}, I_E = 0$	-30			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = -1\text{mA}, I_B = 0$	-25			V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = -10\mu\text{A}, I_C = 0$	-6			V
I_{CBO}	Collector Cut-off Current	$V_{CB} = -20\text{V}, I_E = 0$			-100	nA
I_{EBO}	Emitter Cut-off Current	$V_{BE} = -4\text{V}, I_C = 0$			-100	nA
h_{FE1} h_{FE2}	DC Current Gain	$V_{CE} = -2\text{V}, I_C = -0.1\text{A}$ $V_{CE} = -2\text{V}, I_C = -1.5\text{A}$	100 65		560	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -1.5\text{A}, I_B = -75\text{mA}$		-0.35	-0.6	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -1.5\text{A}, I_B = -75\text{mA}$		-0.85	-1.2	V

Electrical Characteristics (Continued) $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
f_T	Current Gain Bandwidth Product	$V_{CE} = -10\text{V}, I_C = -50\text{mA}$		150		MHz
C_{ob}	Output Capacitance	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		32		pF
t_{ON}	Turn On Time *	$V_{CC} = -12\text{V}, V_{BE} = -5\text{V}$ $I_{B1} = -I_{B2} = -25\text{mA}$ $I_C = -500\text{mA}, R_L = 24\Omega$		60		ns
t_{STG}	Storage Time *			350		ns
t_F	Fall time *			25		ns

 h_{FE} Classification

Classification	R	S	T	U
h_{FE1}	100 ~ 200	140 ~ 280	200 ~ 400	280 ~ 560

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
1121	KSB1121	SOT-89	13"	--	4,000

Typical Performance Characteristics

Figure 1. Static Characteristic

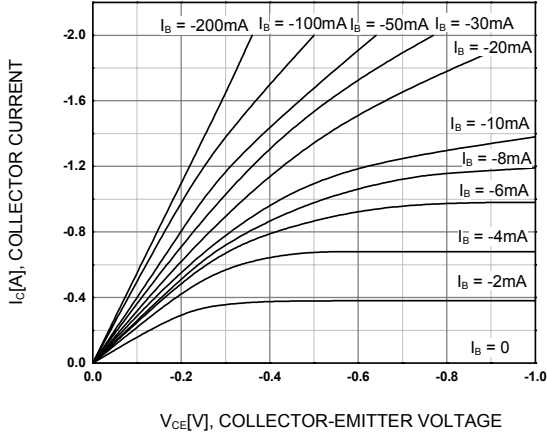


Figure 2. DC Current Gain

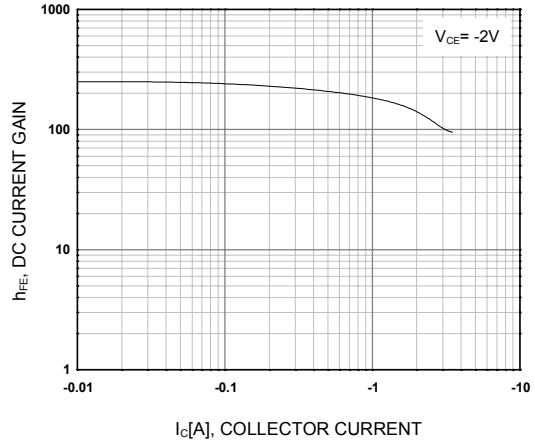


Figure 3. Collector-Emitter Saturation Voltage

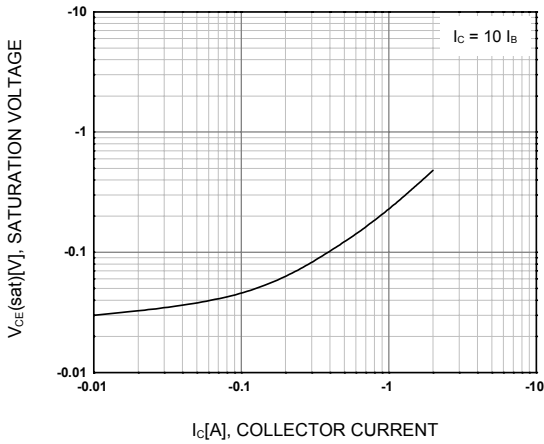


Figure 4. Base-Emitter On Voltage

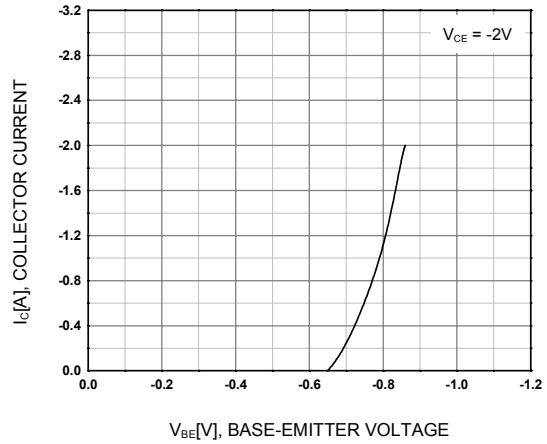


Figure 5. Collector Output Capacitance

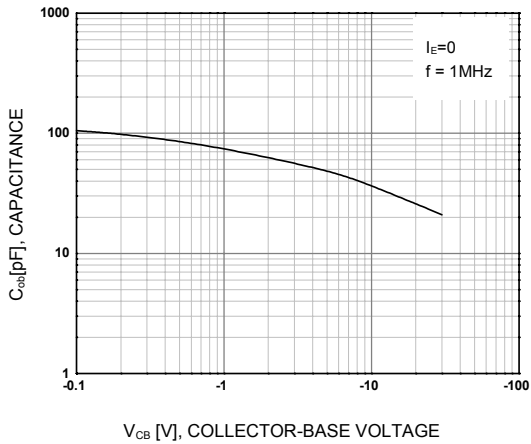
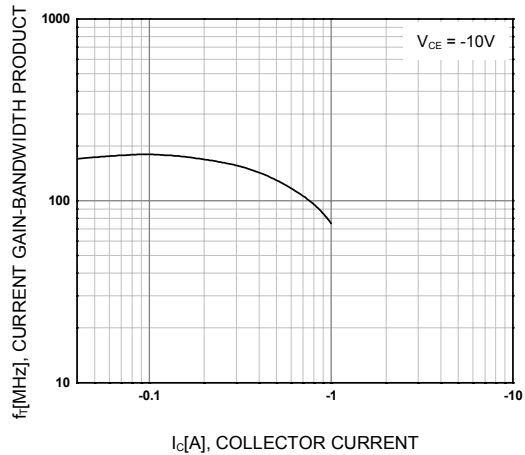
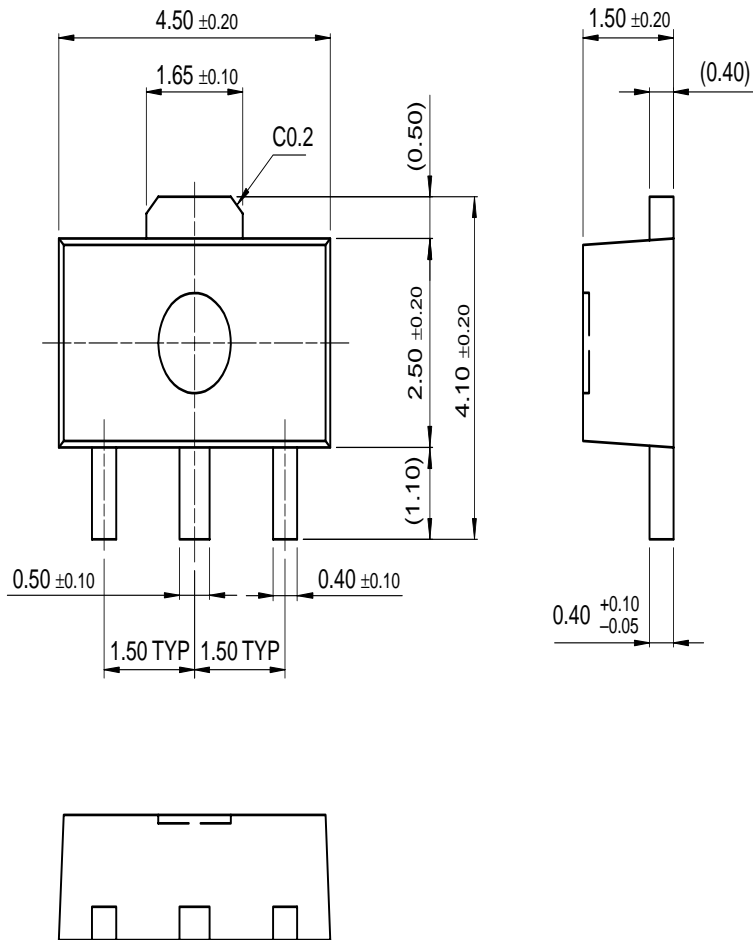


Figure 6. Current Gain Bandwidth Product



Mechanical Dimensions

SOT-89



Dimensions in Millimeters

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Build it Now™	FRFET™	MicroFET™	QS™	TINYOPTO™
CoolFET™	GlobalOptoisolator™	MicroPak™	QT Optoelectronics™	TruTranslation™
CROSSVOLT™	GTO™	MICROWIRE™	Quiet Series™	UHC™
DOME™	HiSeC™	MSX™	RapidConfigure™	UltraFET®
EcoSPARK™	I ² C™	MSXPro™	RapidConnect™	UniFET™
E ² CMOS™	i-Lo™	OCX™	μSerDes™	VCX™
EnSigna™	ImpliedDisconnect™	OCXPro™	SILENT SWITCHER®	Wire™
FACT™	IntelliMAX™	OPTOLOGIC®	SMART START™	
FACT Quiet Series™		OPTOPLANAR™	SPM™	
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The Power Franchise®		POP™	SuperFET™	
Programmable Active Droop™		Power247™	SuperSOT™-3	
		PowerEdge™	SuperSOT™-6	

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PRODUCT STATUS DEFINITIONS

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